

IN THE SPECIFICATION

**Please amend the Title on page 1 as follows:**

SEMICONDUCTOR DEVICE WITH A METAL INSULATOR SEMICONDUCTOR  
TRANSISTOR

**Please amend the Abstract on page 51 as follows:**

ABSTRACT OF THE DISCLOSURE

~~It is an object to provide~~ A semiconductor device capable of holding multibit information in one memory cell ~~also when scaling for a nonvolatile memory progresses~~, and a method of manufacturing the semiconductor device. A trench (TR1) is formed in a channel portion of an MONOS transistor. Then, a source side portion and a drain side portion in a silicon nitride film (122) of a gate insulating film (120) which interpose the trench (TR1) are caused to function as first and second electric charge holding portions capable of holding electric charges (CH1) and (CH2). In the case in which ~~the first~~ electric charges (CH1) are trapped on the drain side and the second electric charges (CH2) are then trapped on the source side, thus, a portion (130a) of a gate electrode (130) in the trench (TR1) functions as a shield. If a fixed potential is given to the gate electrode (130), the second electric charge holding portion is not influenced by an electric field (EF1) induced by the first electric charges (CH1) so that the trapping of the second electric charges (CH2)-is not inhibited.